RAJEEV GANDHI MEMORIAL COLLEGE OF ENGINEERING & TECHNOLOGY (AUTONOMOUS)

DEPARTMENT OF ELECTRONICS & COMMUNICATION ENGINEERING

OTHER JOURNALS

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- Avrajyoti Dutta, Sanjib Kalita, SubhadeepMukhopadhyay; Electrical Characteristics of Nanoelectronic Double-Heterojunction High Electron Mobility Transistors; *Journal of Semiconductor Devices and Circuits*; Vol. 7, issue. 1, pp 18–28 (2020). (NJ)
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